MICROWAVE SEMICONDUCTOR TECHNICAL DATA

TGI8596-50

FEATURES

- ·BROAD BAND INTERNALLY MATCHED HEMT
- ·HIGH POWER

Pout= 47.0dBm at Pin= 41.0dBm

·HIGH GAIN

GL= 9.0dB at 8.5GHz to 9.6GHz

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 24V IDSset= 1.5A f= 8.5 to 9.6 GHz	dBm	46.0	47.0	_
Drain Current	IDS1		Α	_	5.0	6.0
Power Added Efficiency	ηadd	@Pin= 41.0dBm	%	_	31	_
Linear Gain	GL	@Pin= 20dBm	dB	7.0	9.0	_
Channel Temperature Rise	∆Tch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C		130	150

Recommended Gate Resistance(Rg): 13.3 Ω (TYP.)

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 5.0A	S	_	4.5	_
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 23mA	V	-2.6	-4.0	-6.0
Saturated Drain Current	IDSS	VDS= 5V VGS= 0V	А	_	15.0	18.0
Gate-Source Breakdown Voltage	VGSO	IGS= -10mA	٧	-10.0		_
Thermal Resistance	Rth(c-c)	Channel to Case	∘C/W	_	1.4	1.6

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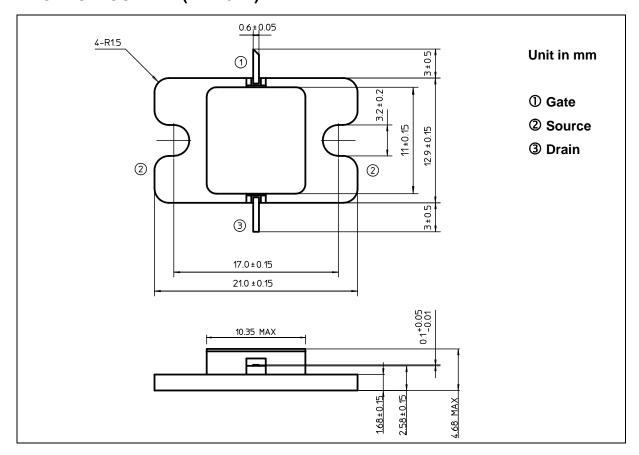


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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	А	15.0
Total Power Dissipation (Tc= 25 °C)	PT	W	140
Channel Temperature	Tch	°C	250
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA04A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.